

INK011BAP1

High Speed Switching
Silicon N-channel MOSFET

DESCRIPTION

INK011BAP1 is a Silicon N-channel MOSFET.

This product is most suitable for use such as portable machinery, because voltage drive and low on resistance.

FEATURE

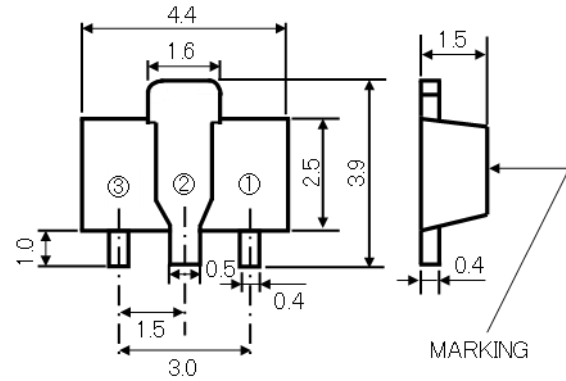
- Input impedance is high, and not necessary to consider a drive electric current.
- High drain current $I_D=1.2A$
- Drive voltage 4.0V
- High power dissipation $P_D=1.0W$ (package mounted on substrate)

FEATURE

Switching

OUTLINE DRAWING

UNIT: mm



TERMINAL CONNECTER

- ①: GATE
- ②: DRAIN
- ③: SOURCE

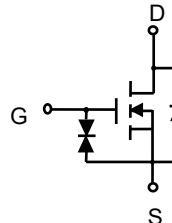
JEITA: SC-62

JEDEC: SOT-89

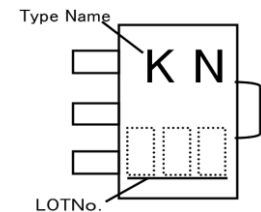
MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Rating	Unit
V _{DSS}	Drain-Source Voltage	150	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current(DC)	1.2	A
P _D	Total Power Dissipation※2	0.5	W
		1.0(※1)	
T _{ch}	Channel Temperature	+150	°C
T _{stg}	Storage temperature	-55~+150	°C

EQUIVALENT CIRCUIT



MARKING



※1: package mounted on glass-epoxy substrate (20mm × 20mm × 1mm, Cu pad 257mm²).

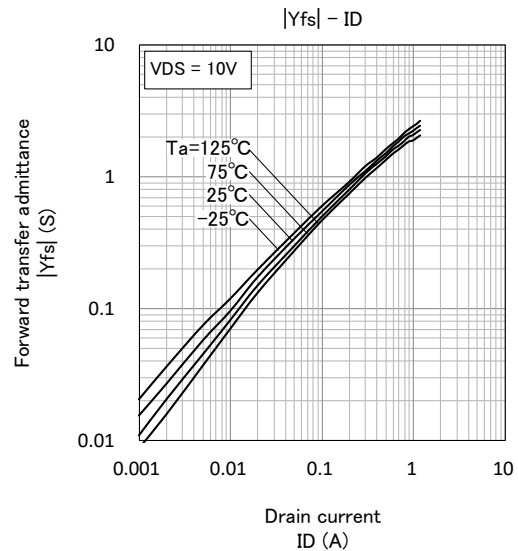
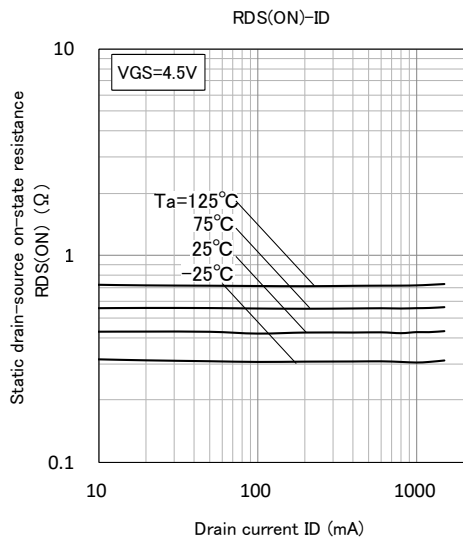
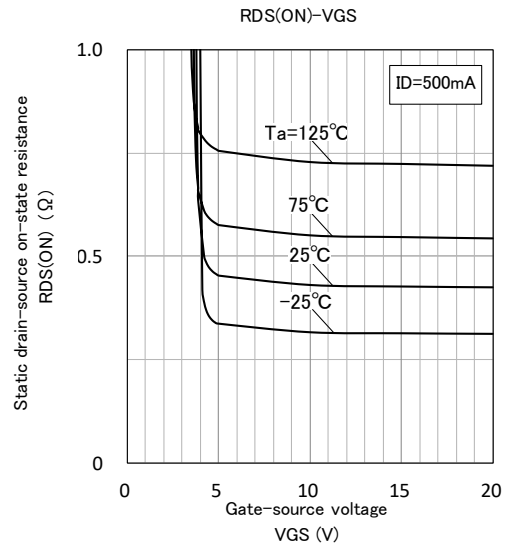
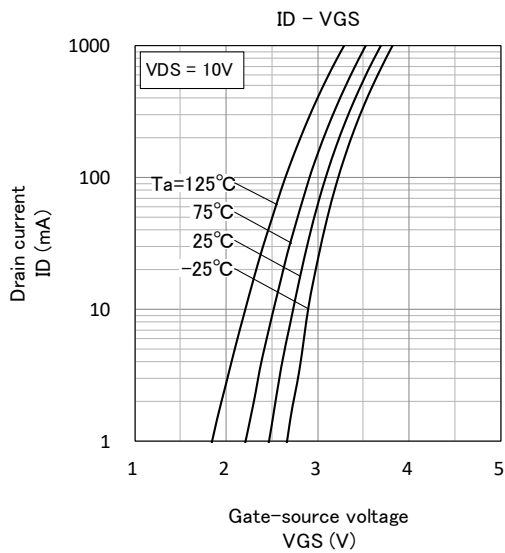
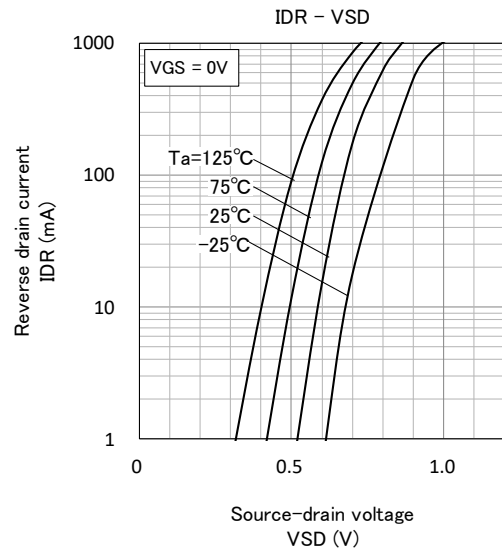
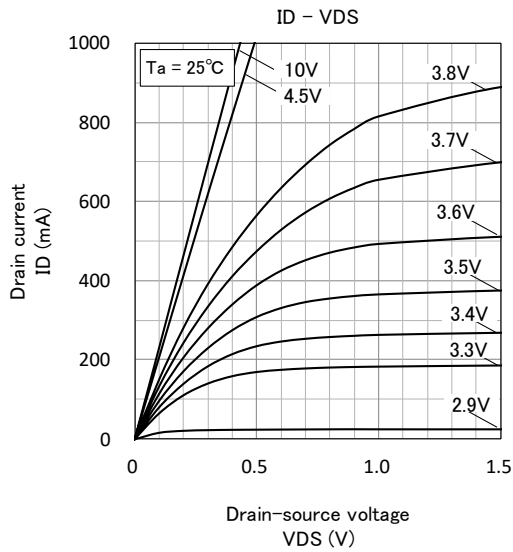
ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	V(BR)DSS	I _D =100 μA, V _{GS} =0V	150	-	-	V
Gate-Source Leak current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V, V _{GS} =0V	-	-	1.0	μA
Gate Threshold Voltage	V _{th}	I _D =250 μA, V _{DS} =V _{GS}	1.0	-	2.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =10V, I _D =1A	-	3.0	-	S
Static Drain-Source On-State Resistance	R _{DS(ON)}	I _D =0.5A, V _{GS} =4.5V	-	0.5	0.8	Ω
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz	-	220	-	pF
Output Capacitance	C _{oss}		-	55	-	pF
Switching Time	t _{on}	V _{DD} =30V, I _D =1A	-	260	-	ns
	t _{off}	V _{GS} =0~5V	-	1660	-	ns

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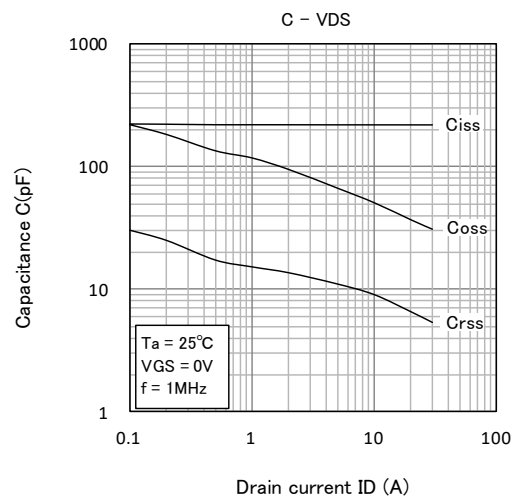
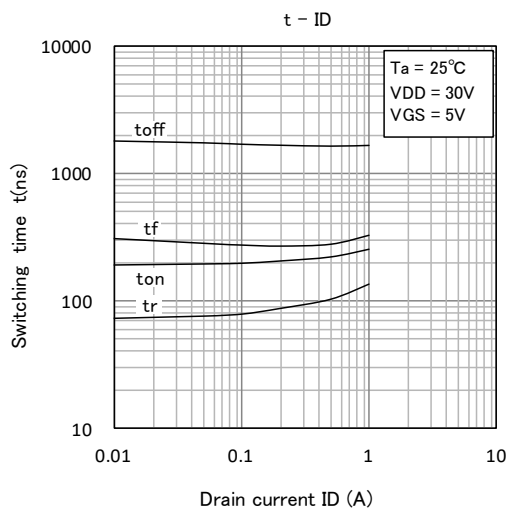
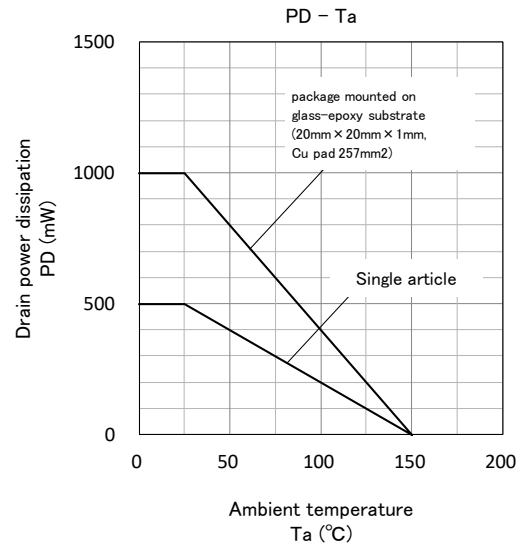
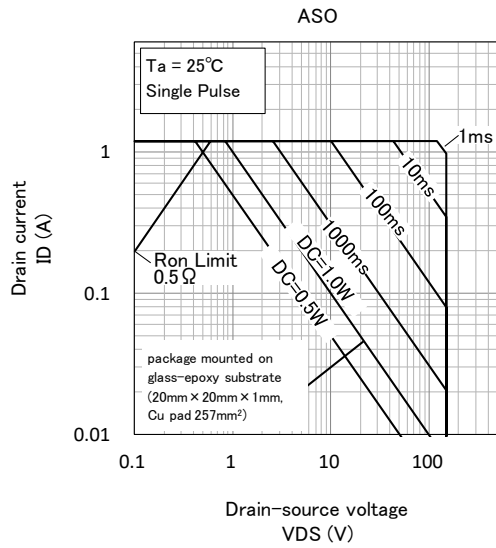
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TYPICAL CHARACTERISTICS

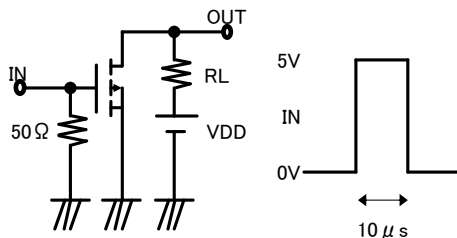


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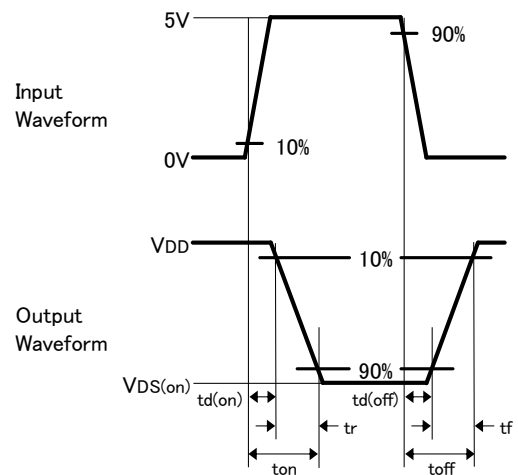
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Switching time test circuit



Duty $\leq 1\%$
Input: $t_r, t_f < 10\text{ns}$
 $V_{DD} = 30\text{V}$
Common source
 $T_a = 25^\circ\text{C}$



Keep safety first in your circuit designs!

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